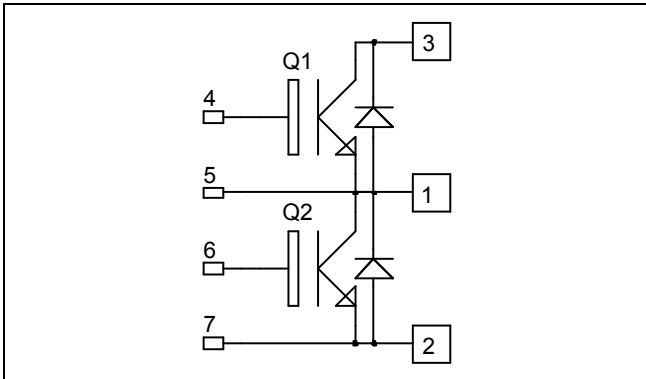


*Phase leg  
Trench + Field Stop IGBT3  
Power Module*

**$V_{CES} = 1700V$   
 $I_C = 300A @ T_c = 80^\circ C$**



### Application

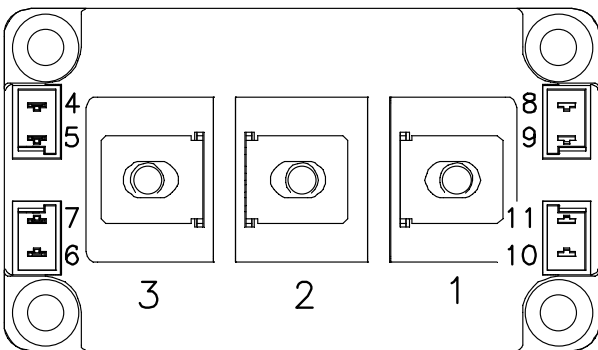
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant



### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1700	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	400
		$T_C = 80^\circ C$	300
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	600
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	1470
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	600A@1650V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$			3	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 300A$				
		$T_j = 25^\circ\text{C}$		2.0	2.5	V
		$T_j = 125^\circ\text{C}$		2.4		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 12\text{ mA}$	5.2	5.8	6.4	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		27		nF
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.9		
$Q_G$	Gate charge	$V_{GE} = \pm 15V, I_C = 300A$ $V_{CE} = 900V$		3.5		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 300A$ $R_G = 4.7\Omega$		280		ns
$T_r$	Rise Time			80		
$T_{d(off)}$	Turn-off Delay Time			850		
$T_f$	Fall Time			120		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 300A$ $R_G = 4.7\Omega$		300		ns
$T_r$	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			1000		
$T_f$	Fall Time			200		
$E_{on}$	Turn On Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 900V$				mJ
		$T_j = 25^\circ\text{C}$		71		
		$T_j = 125^\circ\text{C}$		105		
		$I_C = 300A$		64		
$E_{off}$	Turn Off Energy	$R_G = 4.7\Omega$				
		$T_j = 125^\circ\text{C}$		94		
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 1000V$ $t_p \leq 10\mu\text{s}; T_j = 125^\circ\text{C}$		1200		A

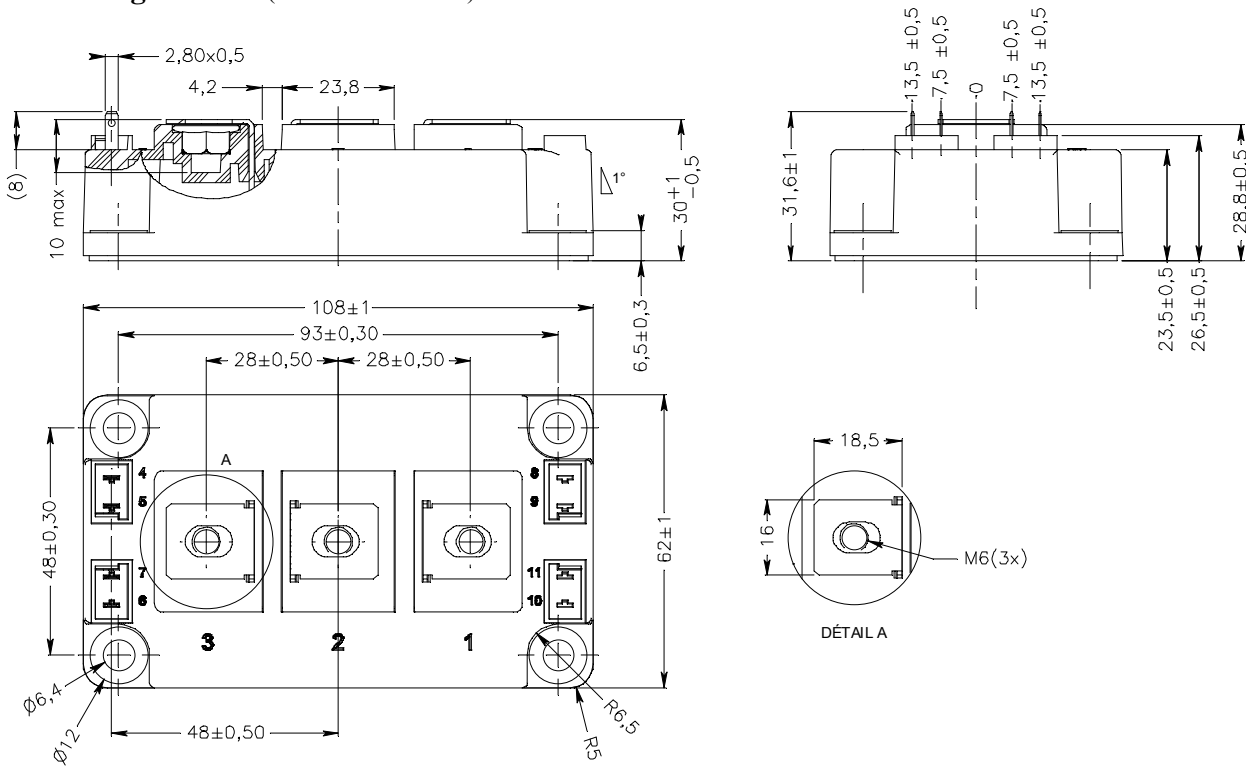
**Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1700			V
$I_{RRM}$	Maximum Reverse Leakage Current	$V_R = 1700V$				$\mu\text{A}$
		$T_j = 25^\circ\text{C}$			750	
		$T_j = 125^\circ\text{C}$			1000	
$I_F$	DC Forward Current	$T_c = 80^\circ\text{C}$		300		A
$V_F$	Diode Forward Voltage	$I_F = 300A$				V
		$T_j = 25^\circ\text{C}$		1.8	2.2	
		$T_j = 125^\circ\text{C}$		1.9		
$t_{rr}$	Reverse Recovery Time	$I_F = 300A$ $V_R = 900V$ $di/dt = 3500A/\mu\text{s}$				ns
			$T_j = 25^\circ\text{C}$		385	
			$T_j = 125^\circ\text{C}$		490	
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		76	
		$T_j = 125^\circ\text{C}$		124		
$E_{rr}$	Reverse Recovery Energy	$T_j = 25^\circ\text{C}$		35		mJ
		$T_j = 125^\circ\text{C}$		70		

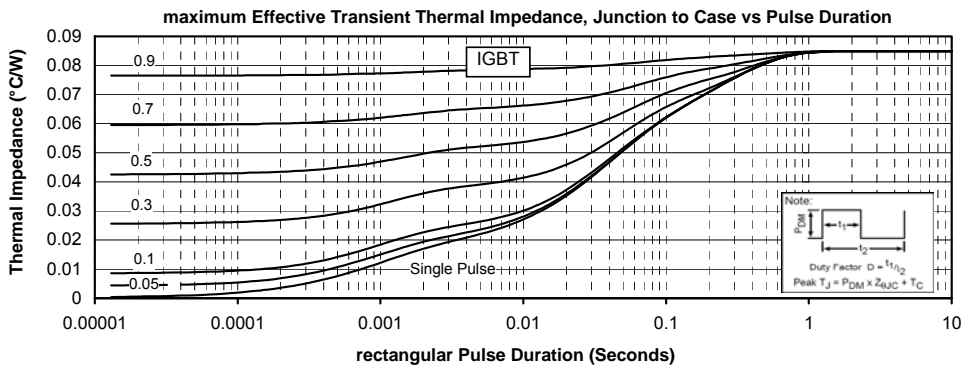
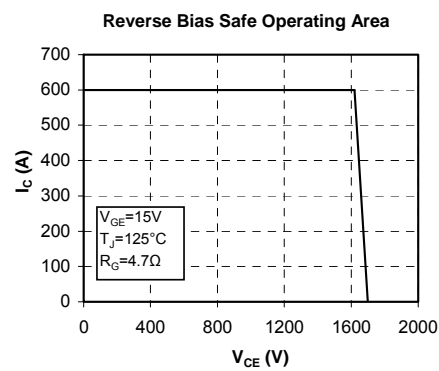
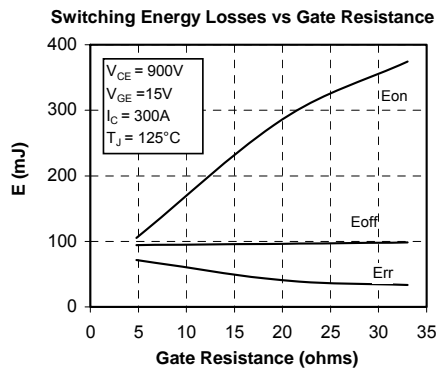
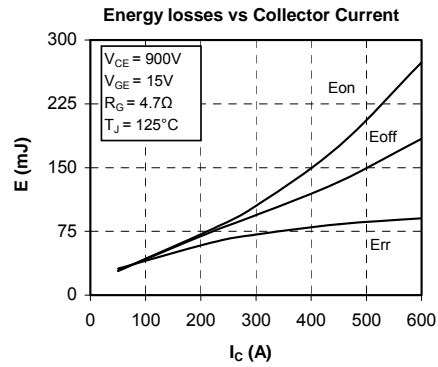
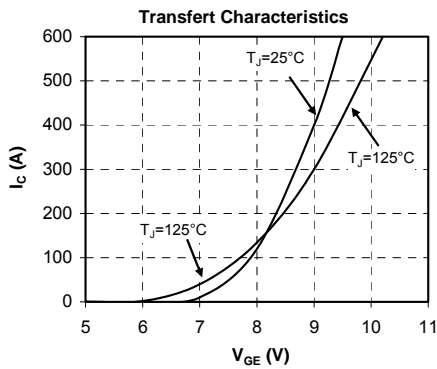
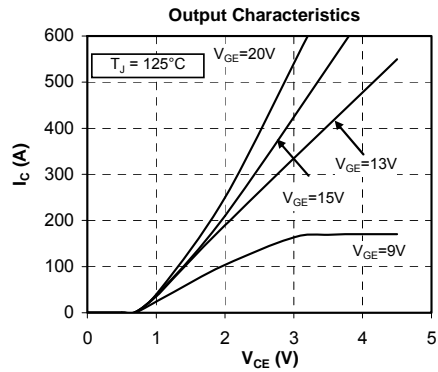
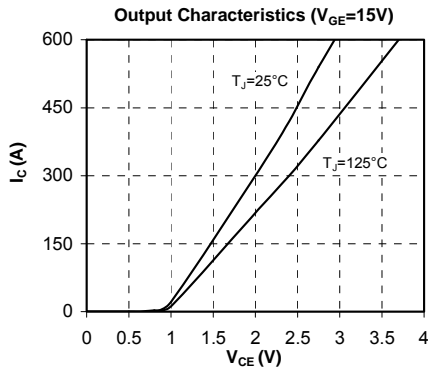
## Thermal and package characteristics

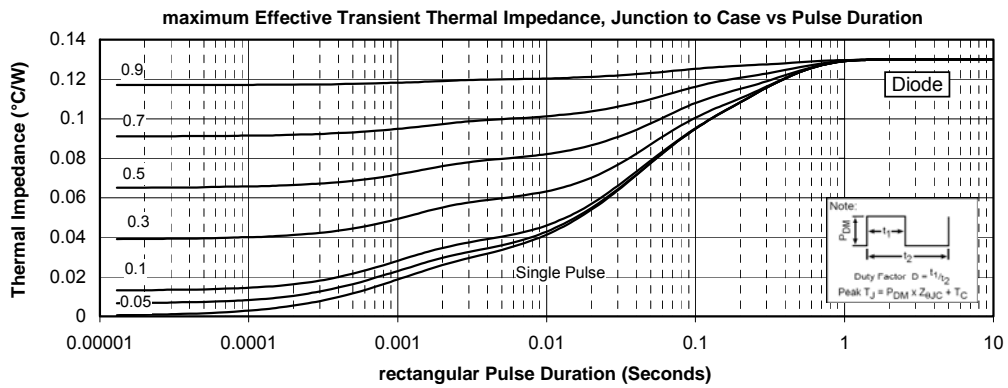
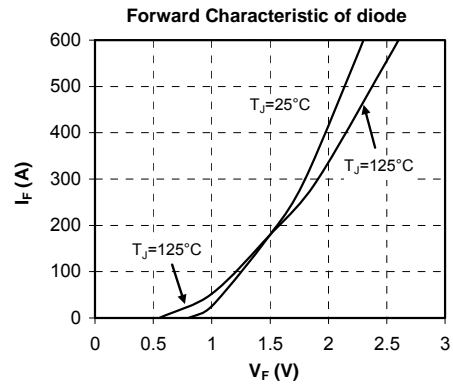
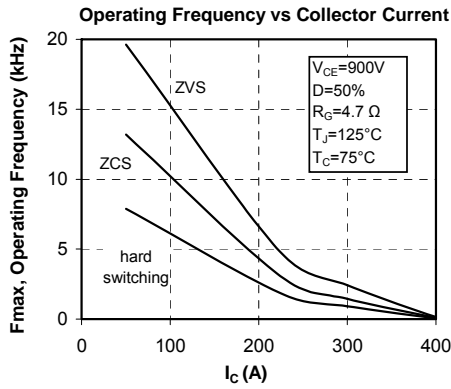
Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.085	°C/W	
		Diode		0.13		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	4000			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		125		
Torque	Mounting torque	For terminals	M6	3	5	N.m
		To Heatsink	M6	3	5	
Wt	Package Weight			350	g	

## D3 Package outline (dimensions in mm)



## Typical Performance Curve





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